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(54) **Title**: METHOD FOR COPPER PLATING THROUGH SILICON VIAS USING WET WAFER BACK CONTACT

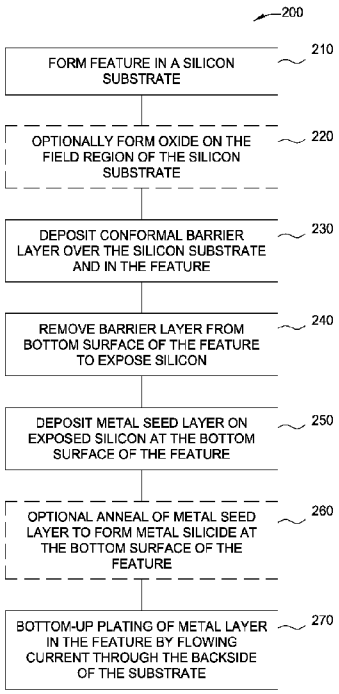



FIG. 2

(57) **Abstract**: A method and apparatus for processing a substrate are provided. In some implementations, the method comprises providing a silicon substrate having an aperture containing an exposed silicon contact surface at a bottom of the aperture, depositing a metal seed layer on the exposed silicon contact surface and exposing the substrate to an electroplating process by flowing a current through a backside of the substrate to form a metal layer on the metal seed layer.

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